

Unit 1 /

Unit

Unit

μA

mA

nA

μC

nF

pF

ns

ns

$I_c(A)$

$V_{GE} \quad V$

Figure 3. Typical Transfer characteristics IGBT

$E_{on}E_{off}(mJ)$

R_G

$E_{on}E_{off}(mJ)$

$I_c \quad A$

Figure 5. Switching Energy vs Collector Current IGBT

$I_c(A)$

$V_{CE} \quad V$

Figure 6. Reverse Biased Safe Operating Area IGBT

$I_F(A)$

$E_{REC}(mJ)$

$V_F V$

R_G

Figure 7. Diode Forward Characteristics Diode

Figure 8. Switching Energy vs Gate Resistor Diode

$E_{REC}(mJ)$

$Z_{thjc}(K/W)$

$I_F A$

Rectangular Pulse Duration s

Figure 9. Switching Energy vs Forward Current Diode

Figure 10. Transient Thermal Impedance of Diode and IGBT



Dimensions in (mm)
Figure 11. Package Outline